

Preliminary Amendment

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Title: BIPOLAR TRANSISTOR

IN THE ABSTRACT

Please replace the Abstract with the following rewritten paragraph:

Abstract

Bipolar transistor

~~To reduce the extrinsic base resistance and thus to achieve a low resistance base electrode of a bipolar transistor, as the base electrode (2) a polysilicon layer, into which impurity atoms, particularly C atoms, which cause a high density of vacancies in the polysilicon layer, are inserted, is used.~~

BIPOLAR TRANSISTOR

Abstract

A bipolar transistor and method of making a bipolar transistor is disclosed. In one embodiment, the bipolar transistor includes a polysilicon layer into which impurity atoms are inserted, thereby reducing the layer resistance.